

TECHNICAL DATA
DATA SHEET 4151, REV. B

LOW R_{DS} HERMETIC POWER MOSFET - N-CHANNEL

FEATURES:

- 100 Volt, 0.011 Ohm, 90A MOSFET for Glidcop version
- Isolated Hermetic Metal Package
- Ultra Low $R_{DS(on)}$
- Ceramic Seals with Glidcop leads (SHDCG224701)

MAXIMUM RATINGS

ALL RATINGS ARE AT $T_C = 25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	± 20	Volts
ON-STATE DRAIN CURRENT	I_{D25}	-	-	70*	Amps
PULSED DRAIN CURRENT	I_{DM}	-	-	240	Amps
OPERATING AND STORAGE TEMPERATURE	T_J/T_{STG}	-55	-	+150	$^\circ\text{C}$
TOTAL DEVICE DISSIPATION	P_D	-	-	210	Watts
THERMAL RESISTANCE, JUNCTION TO CASE	$R_{\theta JC}$	-	-	0.6	$^\circ\text{C}/\text{W}$

Note: * current limited by package; die rating is 90A

ELECTRICAL CHARACTERISTICS

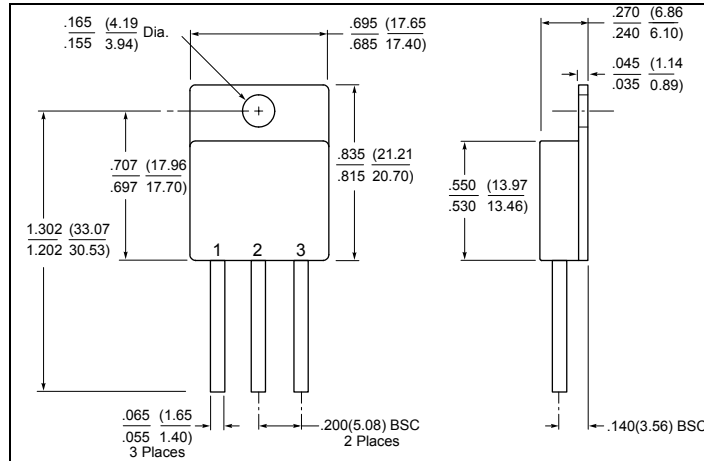
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS
DRAIN TO SOURCE BREAKDOWN VOLTAGE $V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	BV_{DSS}	100	-	-	Volts
STATIC DRAIN TO SOURCE ON STATE RESISTANCE $V_{GS} = 10\text{V}, I_D = 30\text{A}$	$R_{DS(ON)}$ Glidcop Version	-	0.011	0.013	Ω
STATIC DRAIN TO SOURCE ON STATE RESISTANCE $V_{GS} = 10\text{V}, I_D = 30\text{A}$	$R_{DS(ON)}$ Standard Version	-	0.013	0.015	Ω
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	$V_{GS(th)}$	2	-	4	Volts
FORWARD TRANSCONDUCTANCE $V_{DS} = 15\text{V}, I_D = 30\text{A}$	g_{fs}	25	-	-	$\text{S}(1/\Omega)$
ZERO GATE VOLTAGE DRAIN CURRENT $V_{DS} = 0.8 \times \text{Max. rating}, V_{GS} = 0\text{V}, T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	I_{DSS}	-	-	1 50	μA
GATE TO SOURCE LEAKAGE FORWARD $V_{GS} = 20\text{V}$ GATE TO SOURCE LEAKAGE REVERSE $V_{GS} = -20\text{V}$	I_{GSS}	-	-	100 -100	nA
TURN ON DELAY TIME $V_{DD} = 50\text{V}$ RISE TIME $I_D = 55\text{A}$	$t_{d(ON)}$ t_r	-	20 110	30 170	nsec
TURN OFF DELAY TIME $V_{GS} = 10\text{V}$ FALL TIME $R_G = 2.5\Omega$	$t_{d(OFF)}$ t_f	-	65 100	100 150	nsec
DIODE FORWARD VOLTAGE $I_F = 30\text{A}, V_{GS} = 0\text{V}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2\%$	V_{SD}	-	1.0	1.2	Volts
REVERSE RECOVERY TIME $T_J = 25^\circ\text{C}$, $I_F = 30\text{A}, V_R = 100\text{V}$ $di/dt = 100\text{A}/\mu\text{sec}$	t_{rr}	-	70	140	nsec
INPUT CAPACITANCE $V_{GS} = 0\text{V}$, OUTPUT CAPACITANCE $V_{DS} = 25\text{V}$, REVERSE TRANSFER CAPACITANCE $f = 1.0\text{MHz}$	C_{iss} C_{oss} C_{rss}	-	8700 740 450	-	pF

SENSITRON

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MECHANICAL DIMENSIONS: in Inches / mm



TO-258

DEVICE TYPE	PIN-1	PIN-2	PIN-3
N-CHANNEL MOSFET TO-258 PACKAGE	DRAIN	SOURCE	GATE

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